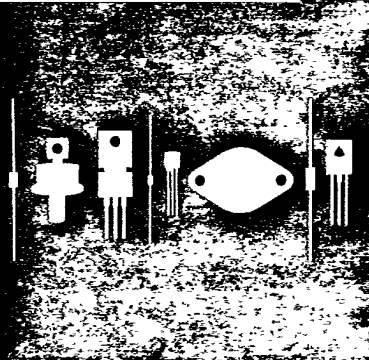


Central
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145 Adams Avenue
Hauppauge, New York 11788



CQ92A
CQ92B
CQ92D
CQ92M

TRIAC
0.8 AMPS
100 THRU 600 VOLTS

JEDEC TO-92 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR CQ92A series types are epoxy molded silicon triacs designed for full wave AC control applications featuring gate triggering in all four (4) quadrants.

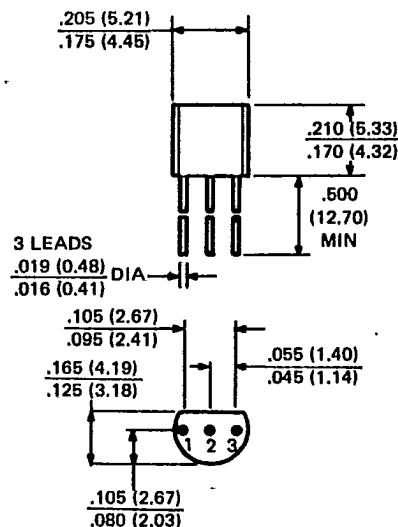
MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL	CQ92A	CQ92B	CQ92D	CQ92M	UNIT
Peak Repetitive Off-State Voltage	V_{DRM}	100	200	400	600	V
RMS On-State Current	$I_T(\text{RMS})$		0.8			A
Peak One Cycle Surge (10ms)	I_{TSM}		8.0			A
Peak Gate Current	I_{GM}		1.0			A
Average Gate Power Dissipation	$P_G(\text{AV})$		0.1			W
Operating and Storage Junction Temperature	T_J, T_{STG}	-65 TO +150				$^\circ\text{C}$
Thermal Resistance	θ_{JA}	210				$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_{DRM}	$V_D = \text{Rated } V_{DRM}, T_C = 100^\circ\text{C}$			2.0	mA
V_{TM}	$I_T = 1.12\text{A}$			1.5	V
I_{GT}	$V_D = 12\text{V}$, Quad I (MT2+, G+)			5.0	mA
I_{GT}	$V_D = 12\text{V}$, Quad II (MT2+, G-)			5.0	mA
I_{GT}	$V_D = 12\text{V}$, Quad III (MT2-, G-)			5.0	mA
I_{GT}	$V_D = 12\text{V}$, Quad IV (MT2-, G+)			5.0	mA
V_{GT*}	$V_D = 12\text{V}$			2.0	V
I_H	$V_D = 12\text{V}$			10	mA
dv/dt	Exponential Rise to $V_D = V_{DRM}, T_C = 100^\circ\text{C}$		50		V/ μs

OUTLINE DRAWING:



LEAD CODE:

1. MT1
2. GATE
3. MT2

*In all four (4) Quadrants

R2